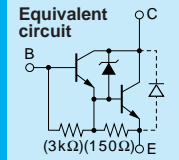


Built-in Avalanche Diode  
for Surge Absorbing  
Darlington

# 2SD1796



Silicon NPN Triple Diffused Planar Transistor

Application : Driver for Solenoid, Relay and Motor and General Purpose

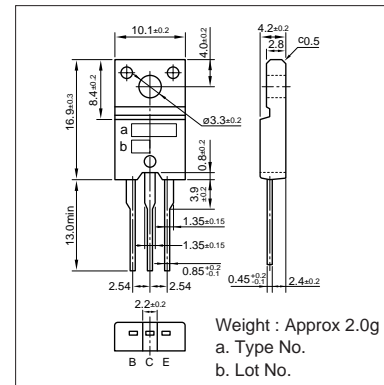
**Absolute maximum ratings** (Ta=25°C)

Symbol	2SD1796	Unit
V <sub>CB0</sub>	60±10	V
V <sub>CEO</sub>	60±10	V
V <sub>EBO</sub>	6	V
I <sub>C</sub>	4	A
I <sub>B</sub>	0.5	A
P <sub>C</sub>	25(T <sub>C</sub> =25°C)	W
T <sub>J</sub>	150	°C
T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics** (Ta=25°C)

Symbol	Conditions	2SD1796	Unit
I <sub>CB0</sub>	V <sub>CB</sub> =50V	10max	μA
I <sub>EBO</sub>	V <sub>EB</sub> =6V	10max	mA
V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA	60±10	V
h <sub>FE</sub>	V <sub>CE</sub> =4V, I <sub>C</sub> =3A	2000min	
V <sub>CE(sat)</sub>	I <sub>C</sub> =3A, I <sub>B</sub> =10mA	1.5max	V
f <sub>r</sub>	V <sub>CE</sub> =12V, I <sub>E</sub> =-0.2A	60typ	MHz
C <sub>OB</sub>	V <sub>CB</sub> =10V, f=1MHz	45 typ	pF

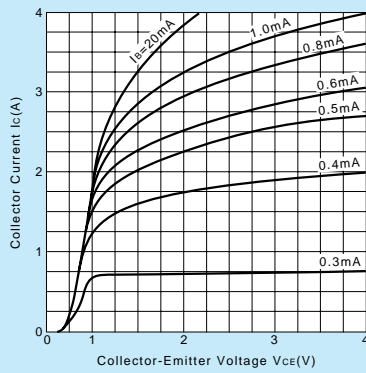
**External Dimensions FM20(TO220F)**



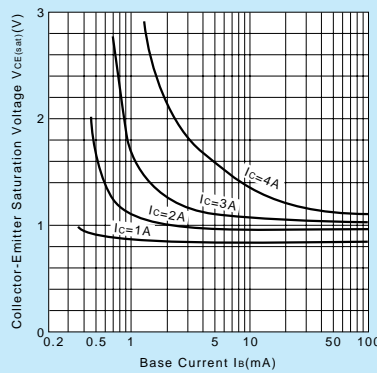
**Typical Switching Characteristics (Common Emitter)**

V <sub>CC</sub> (V)	R <sub>L</sub> (Ω)	I <sub>C</sub> (A)	V <sub>BB1</sub> (V)	V <sub>BB2</sub> (V)	I <sub>B1</sub> (mA)	I <sub>B2</sub> (mA)	t <sub>on</sub> (μs)	t <sub>stg</sub> (μs)	t <sub>f</sub> (μs)
30	10	3	10	-5	10	-10	1.0typ	4.0typ	1.5typ

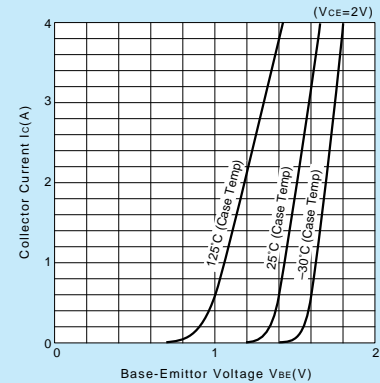
**I<sub>C</sub>-V<sub>CE</sub> Characteristics (Typical)**



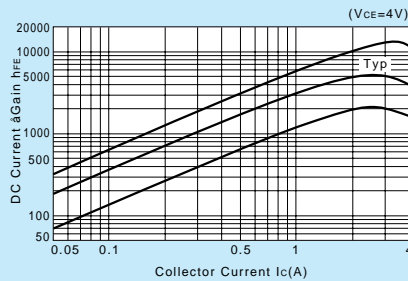
**V<sub>CE(sat)</sub>-I<sub>B</sub> Characteristics (Typical)**



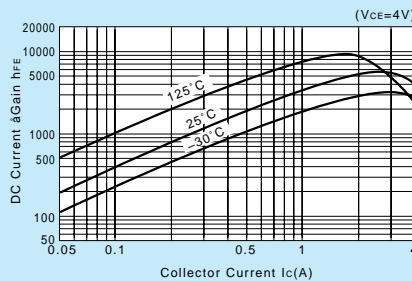
**I<sub>C</sub>-V<sub>BE</sub> Temperature Characteristics (Typical)**



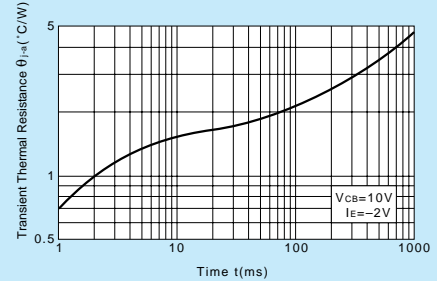
**h<sub>FE</sub>-I<sub>C</sub> Characteristics (Typical)**



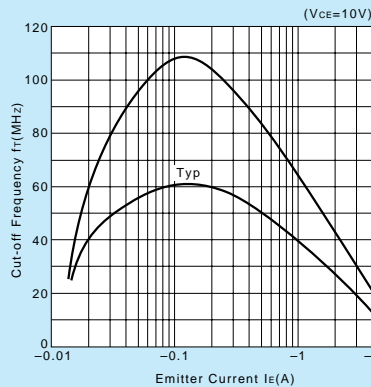
**h<sub>FE</sub>-I<sub>C</sub> Temperature Characteristics (Typical)**



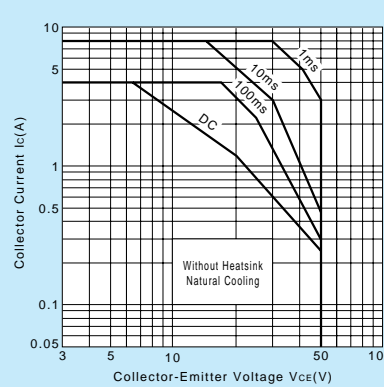
**θ<sub>J-a</sub>-t Characteristics**



**f<sub>r</sub>-I<sub>E</sub> Characteristics (Typical)**



**Safe Operating Area (Single Pulse)**



**P<sub>C</sub>-T<sub>a</sub> Derating**

